Takashi Kita

List of Publications by Citations

223	3,033	28	46
papers	citations	h-index	g-index
272	3,418	2.6	4.93
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
223	Intermediate band solar cells: Recent progress and future directions. *Applied Physics Reviews*, **2015**, 2, 021302	17.3	222
222	Increase in photocurrent by optical transitions via intermediate quantum states in direct-doped InAs/GaNAs strain-compensated quantum dot solar cell. *Journal of Applied Physics*, **2011**, 109, 024301	2.5	174
221	Temperature Dependence of GaAs1-xBixBand Gap Studied by Photoreflectance Spectroscopy. *Japanese Journal of Applied Physics*, **2003**, 42, 371-374	1.4	164
220	Grain-size effects on dielectric phase transition of BaTiO3 ceramics. *Solid State Communications*, **1987**, 62, 765-767	1.6	142
219	Valence-band splitting in ordered Ga0.5In0.5P studied by temperature-dependent photoluminescence polarization. *Physical Review B*, **1992**, 45, 6637-6642	3.3	89
218	Epitaxial growth of LiNbO3-LiTaO3 thin films on Al2O3. *Journal of Applied Physics*, **1987**, 62, 2989-2993	2.5	75
217	Polarization-Independent Photoluminescence from Columnar InAs/GaAs Self-Assembled Quantum Dots. *Japanese Journal of Applied Physics*, **2002**, 41, L1143-L1145	1.4	69
216	Artificial control of optical gain polarization by stacking quantum dot layers. *Applied Physics Letters*, **2006**, 88, 211106	3.4	68
215	Two-step photon up-conversion solar cells. *Nature Communications*, **2017**, 8, 14962	17.4	66
214	Control of optical polarization anisotropy in edge emitting luminescence of InAs/GaAs self-assembled quantum dots. *Applied Physics Letters*, **2004**, 84, 1820-1822	3.4	48
213	Photoreflectance characterization of surface Fermi level in as-grown GaAs(100). *Journal of Applied Physics*, **1990**, 68, 5309-5313	2.5	42
212	Raman and x-ray scattering from ultrafine semiconductor particles. *Journal of Applied Physics*, **1987**, 61, 969-971	2.5	42
211	Zone-Folding Effects on Phonons in GaAs-AlAs Superlattices. *Japanese Journal of Applied Physics*, **1985**, 24, 1331-1334	1.4	42
210	Optical and magnetic properties in epitaxial GdN thin films. *Physical Review B*, **2011**, 83,	3.3	41
209	Experimental and atomistic theoretical study of degree of polarization from multilayer InAs/GaAs quantum dot stacks. *Physical Review B*, **2011**, 84,	3.3	41
208	One-dimensional miniband formation in closely stacked InAs/GaAs quantum dots. *Physical Review B* , **2013**, 87,	3.3	40
207	Photoluminescence characteristics of quantum dots with electronic states interconnected along growth direction. *Journal of Applied Physics*, **2008**, 103, 113504	2.5	38

206	Multidirectional Observation of Photoluminescence Polarization Anisotropy in Closely Stacked InAs/GaAs Quantum Dots. *Applied Physics Express*, **2011**, 4, 062001	2.4	36
205	Raman study of GaAs-InxAl1 As strained-layer superlattices. *Journal of Applied Physics*, **1985**, 58, 4342-4345	2.5	36
204	Transient photoconductivity responses in amorphous In-Ga-Zn-O films. *Journal of Applied Physics*, **2012**, 112, 053715	2.5	35
203	Electron tomography of embedded semiconductor quantum dot. *Applied Physics Letters*, **2008**, 92, 031902	3.4	35
202	Effects of absorption coefficients and intermediate-band filling in InAs/GaAs quantum dot solar cells. *Applied Physics Letters*, **2010**, 97, 193106	3.4	34
201	Bound exciton states of isoelectronic centers in GaAs:N grown by an atomically controlled doping technique. *Physical Review B*, **2006**, 74,	3.3	34
200	Electroreflectance polarization study of valence-band states in ordered Ga0.5In0.5P. *Applied Physics Letters*, **1993**, 63, 512-514	3.4	34
199	Polarization control of electroluminescence from vertically stacked InAs/GaAs quantum dots. *Applied Physics Letters*, **2010**, 96, 211906	3.4	31
198	Vertical-geometry all-optical switches based on InAs/GaAs quantum dots in a cavity. *Applied Physics Letters*, **2009**, 95, 021109	3.4	31
197	Two-step photon absorption in InAs/GaAs quantum-dot superlattice solar cells. *Physical Review B*, **2015**, 91,	3.3	29
196	Carrier dynamics of the intermediate state in InAs/GaAs quantum dots coupled in a photonic cavity under two-photon excitation. *Physical Review B*, **2012**, 86,	3.3	29
195	Effect of internal electric field on InAs/GaAs quantum dot solar cells. *Journal of Applied Physics*, **2014**, 115, 083510	2.5	27
194	Dynamic process of anti-Stokes photoluminescence at a long-range-ordered Ga0.5In0.5P/GaAs heterointerface. *Physical Review B*, **1999**, 59, 15358-15362	3.3	27
193	Photoreflectance study on residual strain in heteroepitaxial gallium arsenide on silicon. *Physical Review B*, **1990**, 41, 2936-2943	3.3	27
192	Impurity doping in self-assembled InAs/GaAs quantum dots by selection of growth steps. *Journal of Applied Physics*, **2010**, 108, 063524	2.5	25
191	Optical reflectance study of the wetting layers in (In, Ga)As self-assembled quantum dot growth on GaAs (001). *Physical Review B*, **2002**, 66,	3.3	25
190	Suppression of thermal carrier escape and efficient photo-carrier generation by two-step photon absorption in InAs quantum dot intermediate-band solar cells using a dot-in-well structure. *Journal of Applied Physics*, **2014**, 116, 063510	2.5	23
189	Intraband carrier dynamics in InAs/GaAs quantum dots stimulated by bound-to-continuum excitation. *Journal of Applied Physics*, **2013**, 113, 223511	2.5	22

188	Temperature-dependent carrier tunneling for self-assembled InAs/GaAs quantum dots with a GaAsN quantum well injector. *Applied Physics Letters*, **2010**, 96, 151104	3.4	22
187	Suppression of nonradiative recombination process in directly Si-doped InAs/GaAs quantum dots. *Journal of Applied Physics*, **2011**, 110, 103511	2.5	21
186	Fine structure splitting of isoelectronic bound excitons in nitrogen-doped GaAs. *Physical Review B*, **2008**, 77,	3.3	20
185	High-Brightness Electron Emission from Flexible Carbon Nanotube/Elastomer Nanocomposite Sheets. *Japanese Journal of Applied Physics*, **2006**, 45, L1186-L1189	1.4	20
184	The optical processes in AlInP/GaInP/AlInP quantum wells. *Journal of Applied Physics*, **1996**, 80, 4592-4598	2.5	20
183	Deep-level characterization of n-type GaAs by photoreflectance spectroscopy. *Journal of Applied Physics*, **1991**, 69, 3691-3695	2.5	19
182	Saturable Two-Step Photocurrent Generation in Intermediate-Band Solar Cells Including InAs Quantum Dots Embedded in Al$_{0.3}$Ga$_{0.7}$ As/GaAs Quantum Wells. *IEEE Journal of Photovoltaics*, **2016**, 6, 465-472	3.7	18
181	Effect of spacer layer thickness on multi-stacked InGaAs quantum dots grown on GaAs (311)B substrate for application to intermediate band solar cells. *Journal of Applied Physics*, **2012**, 111, 074305	2.5	18
180	Observation of phase shifts in a vertical cavity quantum dot switch. *Applied Physics Letters*, **2011**, 98, 231101	3.4	18
179	Study on spin-splitting phenomena in the band structure of GdN. *Applied Physics Letters*, **2012**, 100, 232410	3.4	18
178	A New Method of Photothermal Displacement Measurement by Laser Interferometric Probe -Its Mechanism and Applications to Evaluation of Lattice Damage in Semiconductors. *Japanese Journal of Applied Physics*, **1992**, 31, 3575-3583	1.4	18
177	Real time analysis of self-assembled InAs/GaAs quantum dot growth by probing reflection high-energy electron diffraction chevron image. *Journal of Applied Physics*, **2008**, 104, 074305	2.5	17
176	Preparation of composition-controlled silicon oxynitride films by sputtering; deposition mechanism, and optical and surface properties. *Applied Physics A: Solids and Surfaces*, **1989**, 49, 305-311		17
175	Nanosecond-scale hot-carrier cooling dynamics in one-dimensional quantum dot superlattices. *Physical Review B*, **2016**, 93,	3.3	16
174	Carbon Nanotube/Aluminum Composites As a Novel Field Electron Emitter. *Japanese Journal of Applied Physics*, **2006**, 45, L650-L653	1.4	16
173	Anisotropic magneto-optical effects in one-dimensional diluted magnetic semiconductors. *Physical Review B*, **2006**, 74,	3.3	16
172	Broadband control of emission wavelength of InAs/GaAs quantum dots by GaAs capping temperature. *Journal of Applied Physics*, **2015**, 118, 154301	2.5	15
171	Photoluminescence from metastable states in long-range ordered (Al0.5Ga0.5)0.51In0.49P. *Physical Review B*, **1997**, 55, 4411-4416	3.3	15

170	Direct optical transitions in indirect-gap (Al0.5Ga0.5)0.51In0.49P by atomic ordering. *Physical Review B*, **1996**, 53, 15713-15718	3.3	15
169	Epitaxial two-dimensional nitrogen atomic sheet in GaAs. *Applied Physics Letters*, **2014**, 104, 041907	3.4	14
168	Efficient two-step photocarrier generation in bias-controlled InAs/GaAs quantum dot superlattice intermediate-band solar cells. *Scientific Reports*, **2017**, 7, 5865	4.9	14
167	Polarization-insensitive optical gain characteristics of highly stacked InAs/GaAs quantum dots. *Journal of Applied Physics*, **2014**, 115, 233512	2.5	14
166	Hot-carrier solar cells using low-dimensional quantum structures. *Applied Physics Letters*, **2014**, 105, 171904	3.4	14
165	Broadband light sources using InAs quantum dots with InGaAs strain-reducing layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 331-333		14
164	Detailed Design and Characterization of All-Optical Switches Based on InAs/GaAs Quantum Dots in a Vertical Cavity. *IEEE Journal of Quantum Electronics*, **2010**, 46, 1582-1589	2	14
163	Narrow-band deep-ultraviolet light emitting device using Al1−xGdxN. *Applied Physics Letters*, **2008**, 93, 211901	3.4	14
162	Photocurrent polarization in long-range ordered Ga0.5In0.5P. *Applied Physics Letters*, **1995**, 66, 1794-1796	3.4	14
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157	Microscopic observation of carrier-transport dynamics in quantum-structure solar cells using a time-of-flight technique. *Applied Physics Letters*, **2015**, 107, 043901	3.4	11
156	Temperature dependence of photoluminescence characteristics of excitons in stacked quantum dots and quantum dot chains. *Journal of Applied Physics*, **2010**, 107, 073506	2.5	11
155	Ferromagnetic properties of GdN thin films studied by temperature dependent circular polarized spectroscopy. *Applied Physics Letters*, **2012**, 101, 072403	3.4	11
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153	Dual chopped photoreflectance spectroscopy for nondestructive characterization of semiconductors and semiconductor nanostructures. *Review of Scientific Instruments*, **2008**, 79, 046110	1.7	11

152	Long-wavelength emission from nitridized InAs quantum dots. *Applied Physics Letters*, **2003**, 83, 4152-4153	3.4	11
151	Observation of quantum beat oscillations and ultrafast relaxation of excitons confined in GaAs thin films by controlling probe laser pulses. *Journal of Applied Physics*, **2012**, 111, 023505	2.5	10
150	Narrowband ultraviolet field-emission device using Gd-doped AlN. *IOP Conference Series: Materials Science and Engineering*, **2009**, 1, 012001	0.4	10
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133	Effect of exciton oscillator strength on upconversion photoluminescence in GaAs/AlAs multiple quantum wells. *Applied Physics Letters*, **2014**, 105, 181901	3.4	7
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131	Bound biexciton luminescence in nitrogen □doped GaAs. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 464-467	1.3	7
130	Influence of local atomic configuration in AlGdN phosphor thin films on deep ultra-violet luminescence intensity. *Journal of Applied Physics*, **2011**, 110, 093108	2.5	7
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114	Reply to: "Thermal artefacts in two-photon solar cell experiments". *Nature Communications*, **2019**, 10, 956	17.4	5
113	Wide-wavelength-range control of photoluminescence polarization in closely stacked InAs/GaAs quantum dots. *Journal of Applied Physics*, **2019**, 125, 234304	2.5	5
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65	Increase in exciton decay rate due to plane-to-plane interaction between cyanine thin films. *AIP Advances*, **2016**, 6, 075209	1.5	3
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